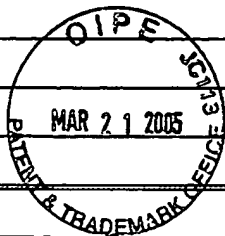


PTO/SB/08A (Substitute for form 1449/PTO)		Attorney Docket No.: 023-0028
		Application No.: 10/729,831
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		First Named Inventor: En-Hsing Chen et al.
		Filing Date: December 5, 2003
		Group Art Unit: 2824 2827
		Examiner Name: Tean K. Lo LyPham
Sheet 1 of 5		Date Submitted: March 15, 2005



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Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
LP	AA	4,142,176	02-27-1979	Dozier		
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LP	AN	JA 62-142363	06-25-1987			
	AO	JA 62-155568	07-10-1987			
	AP	JA-2001-358237	12-26-2001			
	✓ AQ	JA-2002-280467	09-27-2002			
Examiner Signature		Examiner Signature			Date Considered 9/29/05	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional).

²See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04.

³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3)

⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document.

⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible.

⁶Applicant is to place a check mark here if English language Translation is attached.

PTO/SB/08A (Substitute for form 1449/PTO)		Attorney Docket No.: 023-0028
		Application No.: 10/729,831
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		First Named Inventor: En-Hsing Chen et al.
(Continuation Sheet)		Filing Date: December 5, 2003
		Group Art Unit: 2824 2827
		Examiner Name: Joan K. Le Ly Pham
Sheet 2 of 5		Date Submitted: March 15, 2005

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Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	BE					
	BF					
	BG					
	BH					
Examiner Signature: <i>Joan K. Le Ly Pham</i>			Date Considered: 08/29/2005			

PTO/SB/08A (Substitute for form 1449/PTO)		Attorney Docket No.: 023-0028
		Application No.: 10/729,831
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		First Named Inventor: En-Hsing Chen et al.
(Continuation Sheet)		Filing Date: December 5, 2003
		Group Art Unit: 2824 2827
		Examiner Name: Tuan K. Le Ly Pham
Sheet 3 of 5		Date Submitted: March 15, 2005

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Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	BX				
	BY				
Examiner Signature: <i>Pham Tuan K. Le</i>			Date Considered: 02/24/2005		

PTO/SB/08A (Substitute for form 1449/PTO)		Attorney Docket No.: 023-0028
		Application No.: 10/729,831
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		First Named Inventor: En-Hsing Chen et al.
(Continuation Sheet)		Filing Date: December 5, 2003
		Group Art Unit: 2824 2827
		Examiner Name: Joan K. Le Ly Pham
Sheet 4 of 5		Date Submitted: March 15, 2005

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Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	CO					
	CP					
Examiner Signature		Date Considered		08/29/2005		

PTO/SB/08A (Substitute for form 1449/PTO)		Attorney Docket No.: 023-0028
		Application No.: 10/729,831
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		First Named Inventor: En-Hsing Chen et al.
(Continuation Sheet)		Filing Date: December 5, 2003
		Group Art Unit: 3824 2827
		Examiner Name: Toan K. Lo <i>Toan K. Lo</i>
Sheet 5 of 5		Date Submitted: March 15, 2005

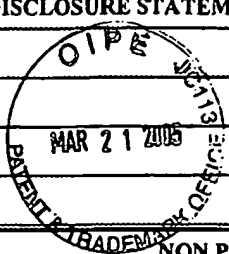
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	DC				

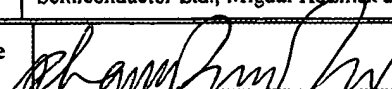
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	DD					
	DE					
	DF					
	DG					
Examiner Signature <i>Toan K. Lo</i>			Date Considered <i>8/24/05</i>			

PTO/SB/08B (Substitute for form 1449/PTO)		Attorney Docket No.: 023-0028	
		Application No.: 10/729,831	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		First Named Inventor: En-Hsing Chen et al.	
		Filing Date: December 5, 2003	
		Group Art Unit: 2824 2827	
		Examiner Name: Joan K. Le Ly Pham	
Sheet 1 of 2		Date Submitted: March 15, 2005	



NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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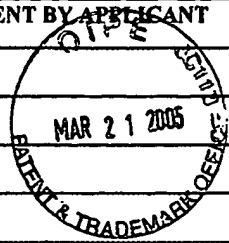
Examiner Signature: 	Date Considered: 3/29/05
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional).

²Applicant is to place a check mark here if English language Translation is attached.

PTO/SB/08B (Substitute for form 1449/PTO)		Attorney Docket No.: 023-0028
		Application No.: 10/729,831
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		First Named Inventor: En-Hsing Chen et al.
(Continuation Sheet)		Filing Date: December 5, 2003
		Group Art Unit: 2824 2827
		Examiner Name: Tuan K. Lo <i>Typhon</i>
Sheet 2 of 2		Date Submitted: March 15, 2005



NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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	AU		
	AV		
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Examiner Signature <i>Tuan K. Lo</i>		Date Considered <i>03/29/05</i>	

U.S. Department of Commerce, Patent and Trademark Office				Attorney Docket No.: 023-0028	
				Application No.: 10/729,831	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant(s): En-Hsing Chen et al.	
				Filing Date: December 5, 2003	
				Group Art Unit: 2824 2827	
				Date Submitted: September 20, 2004	

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*Examiner Initial		Document Number	Date	Name
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	AC	6,005,270	21 Dec 1999	Noguchi
	AD	6,061,270	09 May 2000	Choi
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	AI			
	AJ			
AK				

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					Translation	
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	AM	0 575 051 A1	22 Dec 1993	Europe		/
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	AP					

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)		
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